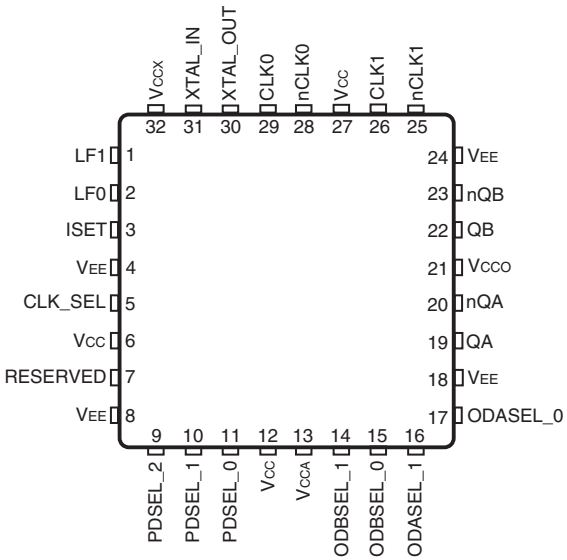
General Description

The 813N252I-04 is a PLL based synchronous multiplier that is optimized for PDH or SONET to Ethernet clock jitter attenuation and frequency translation. The device contains two internal frequency multiplication stages that are cascaded in series. The first stage is a VCXO PLL that is optimized to provide reference clock jitter attenuation. The second stage is a FemtoClock® NG frequency multiplier that provides the low jitter, high frequency Ethernet output clock that easily meets Gigabit and 10 Gigabit Ethernet jitter requirements. Pre-divider and output divider multiplication ratios are selected using device selection control pins. The multiplication ratios are optimized to support most common clock rates used in PDH, SONET and Ethernet applications. The VCXO requires the use of an external, inexpensive pullable crystal. The VCXO uses external passive loop filter components which allows configuration of the PLL loop bandwidth and damping characteristics. The device is packaged in a space-saving 32-VFQFN package and supports industrial temperature range.

Features

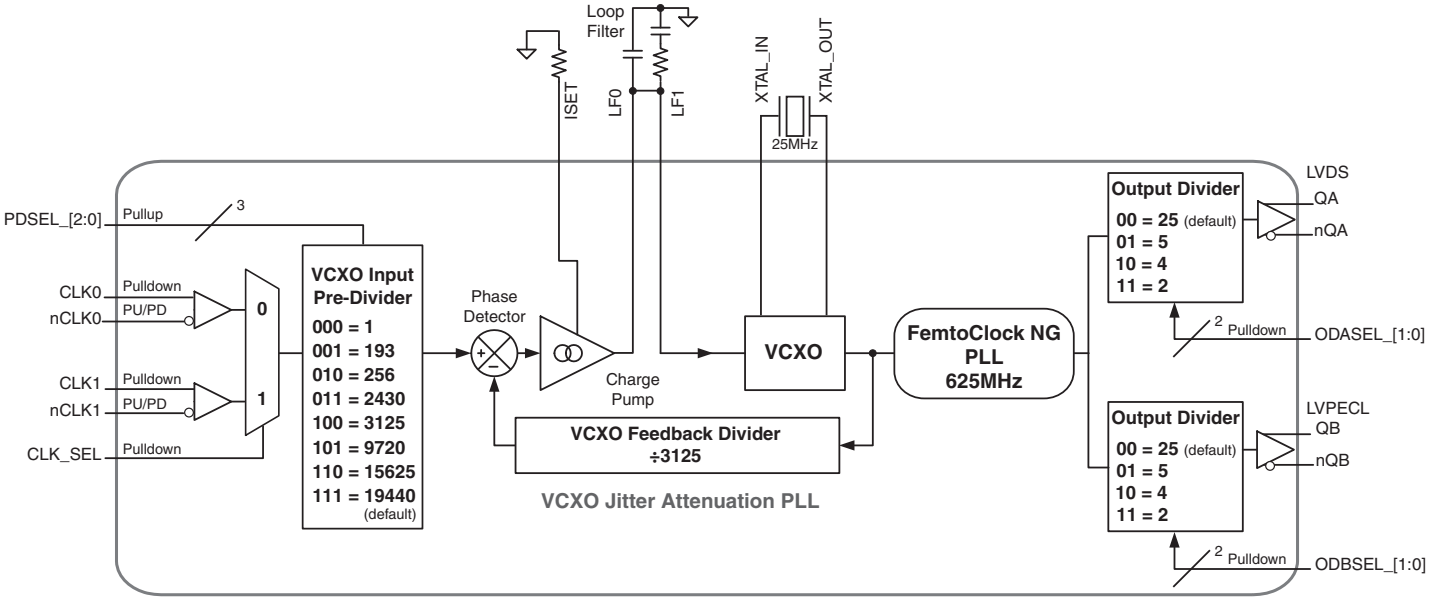
- Fourth generation FemtoClock® Next Generation (NG) technology
- One LVPECL output pair and one LVDS output pair
  Each output supports independent frequency selection at 25MHz, 125MHz, 156.25MHz and 312.5MHz
- Two differential inputs support the following input types: LVPECL, LVDS, LVHSTL, SSTL, HCSL
- Accepts input frequencies from 8kHz to 155.52MHz including 8kHz, 1.544MHz, 2.048MHz, 19.44MHz, 25MHz, 77.76MHz, 125MHz and 155.52MHz
- Attenuates the phase jitter of the input clock by using a low-cost pullable fundamental mode VCXO crystal
- VCXO PLL bandwidth can be optimized for jitter attenuation and reference tracking using external loop filter connection
- FemtoClock NG frequency multiplier provides low jitter, high frequency output
- Absolute pull range: 100ppm
- FemtoClock NG VCO frequency: 625MHz
- RMS phase jitter @ 125MHz, using a 25MHz crystal (12kHz – 20MHz): 0.3ps (typical)
- 3.3V supply voltage
- -40°C to 85°C ambient operating temperature
- Available in lead-free (RoHS 6) package

Pin Assignment



813N252I-04
32 Lead VFQFN
5mm x 5mm x 0.925mm package body
3.15mm x 3.15mm EPad
K Package
Top View

Block Diagram



Pin Description and Pin Characteristic Tables

Table 1. Pin Descriptions

Number	Name	Type		Description
1, 2	LF1, LF0	Analog Input/Output		Loop filter connection node pins. LF0 is the output. LF1 is the input.
3	ISET	Analog Input/Output		Charge pump current setting pin.
4, 8, 18, 24	V_{EE}	Power		Negative supply pins.
5	CLK_SEL	Input	Pulldown	Input clock select. When HIGH selects CLK1, nCLK1. When LOW, selects CLK0, nCLK0. LVCMOS / LVTTL interface levels.
6, 12, 27	V_{CC}	Power		Core supply pins.
7	RESERVED	Reserved		Reserve pin. Do not connect.
9, 10, 11	PDSEL_2, PDSEL_1, PDSEL_0	Input	Pullup	Pre-divider select pins. LVCMOS/LVTTL interface levels. See Table 3A.
13	V_{CCA}	Power		Analog supply pin.
14, 15	ODBSEL_1, ODBSEL_0	Input	Pulldown	Frequency select pins for QB, nQB outputs. See Table 3B. LVCMOS/LVTTL interface levels.
16, 17	ODASEL_1, ODASEL_0	Input	Pulldown	Frequency select pins for QA, nQA outputs. See Table 3B. LVCMOS/LVTTL interface levels.
19, 20	QA, nQA	Output		Differential clock outputs. LVDS interface levels.
21	V_{CCO}	Power		Output supply pin.
22, 23	QB, nQB	Output		Differential clock outputs. LVPECL interface levels.
25	nCLK1	Input	Pullup/ Pulldown	Inverting differential clock input. $V_{CC}/2$ bias voltage when left floating.
26	CLK1	Input	Pulldown	Non-inverting differential clock input.
28	nCLK0	Input	Pullup/ Pulldown	Inverting differential clock input. $V_{CC}/2$ bias voltage when left floating.
29	CLK0	Input	Pulldown	Non-inverting differential clock input.
30, 31	XTAL_OUT, XTAL_IN	Input		Crystal oscillator interface. XTAL_IN is the input. XTAL_OUT is the output.
32	V_{CCX}	Power		Power supply pin for the XTAL oscillator regulator.

NOTE: *Pullup and Pulldown* refer to internal input resistors. See Table 2, *Pin Characteristics,* for typical values.

Table 2. Pin Characteristics

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
C_{IN}	Input Capacitance			4		pF
R_{PULLUP}	Input Pullup Resistor			51		kΩ
$R_{PULLDOWN}$	Input Pulldown Resistor			51		kΩ

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Function Tables

Table 3A. Pre-Divider Selection Function Table

Inputs			
PDSEL_2	PDSEL_1	PDSEL_0	Pre-Divider Value
0	0	0	1
0	0	1	193
0	1	0	256
0	1	1	2430
1	0	0	3125
1	0	1	9720
1	1	0	15625
1	1	1	19440 (default)

Table 3B. Output Divider Function Table

Inputs		
ODxSEL_1	ODxSEL_0	Output Divider Value
0	0	25 (default)
0	1	5
1	0	4
1	1	2

Table 3C. CLK_SEL Function Table

Input	
CLK_SEL	Selected Input
0	CLK0, nCLK0
1	CLK1, nCLK1

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Table 3D. Frequency Function Table

Input Frequency (MHz)	Pre-Divider Value	VCXO Frequency (MHz)	FemtoClock Feedback Divider Value	FemtoClock VCO Frequency (MHz)	Output Divider Value	Output Frequency (MHz)
0.008	1	25	25	625	25	25
0.008	1	25	25	625	5	125
0.008	1	25	25	625	4	156.25
0.008	1	25	25	625	2	312.5
1.544	193	25	25	625	25	25
1.544	193	25	25	625	5	125
1.544	193	25	25	625	4	156.25
1.544	193	25	25	625	2	312.5
2.048	256	25	25	625	25	25
2.048	256	25	25	625	5	125
2.048	256	25	25	625	4	156.25
2.048	256	25	25	625	2	312.5
19.44	2430	25	25	625	25	25
19.44	2430	25	25	625	5	125
19.44	2430	25	25	625	4	156.25
19.44	2430	25	25	625	2	312.5
25	3125	25	25	625	25	25
25	3125	25	25	625	5	125
25	3125	25	25	625	4	156.25
25	3125	25	25	625	2	312.5
77.76	9720	25	25	625	25	25
77.76	9720	25	25	625	5	125
77.76	9720	25	25	625	4	156.25
77.76	9720	25	25	625	2	312.5
125	15625	25	25	625	25	25
125	15625	25	25	625	5	125
125	15625	25	25	625	4	156.25
125	15625	25	25	625	2	312.5
155.52	19440	25	25	625	25	25
155.52	19440	25	25	625	5	125
155.52	19440	25	25	625	4	156.25
155.52	19440	25	25	625	2	312.5

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Absolute Maximum Ratings

NOTE: Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These ratings are stress specifications only. Functional operation of product at these conditions or any conditions beyond those listed in the *DC Characteristics or AC Characteristics* is not implied. Exposure to absolute maximum rating conditions for extended periods may affect product reliability.

Item	Rating
Supply Voltage, V_{CC}	3.63V
Inputs, V_I	-0.5V to V_{CC} + 0.5V
Outputs, I_O (LVPECL) Continuous Current Surge Current Outputs, I_O (LVDS) Continuous Current Surge Current	 50mA 100mA 10mA 15mA
Package Thermal Impedance, θ_{JA}	37°C/W (0 mps)
Storage Temperature, T_{STG}	-65°C to 150°C

DC Electrical Characteristics

Table 4A. Power Supply DC Characteristics, V_{CC} = V_{CCO} = V_{CCX} = 3.3V ± 5%, V_{EE} = 0V, T_A = -40°C to 85°C

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
V_{CC}	Core Supply Voltage		3.135	3.3	3.465	V
V_{CCA}	Analog Supply Voltage		V_{CC} – 0.20	3.3	V_{CC}	V
V_{CCO}	Output Supply Voltage		3.135	3.3	3.465	V
V_{CCX}	Charge Pump Supply Voltage		3.135	3.3	3.465	V
I_{EE}	Power Supply Current				225	mA
I_{CCA}	Analog Supply Current				20	mA
I_{CCX}	Charge Pump Supply Current				20	mA

Table 4B. LVCMOS/LVTTL DC Characteristics, V_{CC} = V_{CCO} = V_{CCX} = 3.3V ± 5%, V_{EE} = 0V, T_A = -40°C to 85°C

Symbol	Parameter		Test Conditions	Minimum	Typical	Maximum	Units
V_{IH}	Input High Voltage			2		V_{CC} + 0.3	V
V_{IL}	Input Low Voltage			-0.3		0.8	V
I_{IH}	Input High Current	CLK_SEL, ODASEL_[0:1], ODBSEL_[0:1]	V_{CC} = V_{IN} = 3.465V			150	µA
		PDSEL_[0:2]	V_{CC} = V_{IN} = 3.465V			10	µA
I_{IL}	Input Low Current	CLK_SEL, ODASEL_[0:1], ODBSEL_[0:1]	V_{CC} = 3.465V, V_{IN} = 0V	-10			µA
		PDSEL_[0:2]	V_{CC} = 3.465, V_{IN} = 0V	-150			µA

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Table 4C. Differential DC Characteristics, V_{CC} = V_{CCO} = V_{CCX} = 3.3V ± 5%, V_{EE} = 0V, T_A = -40°C to 85°C

Symbol	Parameter		Test Conditions	Minimum	Typical	Maximum	Units
I_{IH}	Input High Current	CLK0, nCLK0, CLK1, nCLK1	V_{CC} = V_{IN} = 3.465V			150	µA
I_{IL}	Input Low Current	CLK0, CLK1	V_{CC} = 3.465V, V_{IN} = 0V	-10			µA
		nCLK0, nCLK1	V_{CC} = 3.465V, V_{IN} = 0V	-150			µA
V_{PP}	Peak-to-Peak Input Voltage; NOTE 1			0.15		1.3	V
V_{CMR}	Common Mode Input Voltage; NOTE 1, 2			V_{EE}		V_{CC} – 0.85	V

NOTE 1: V_{IL} should not be less than -0.3V.
NOTE 2: Common mode voltage is defined at the cross point.

Table 4D. LVPECL DC Characteristics, V_{CC} = V_{CCO} = V_{CCX} = 3.3V ± 5%, V_{EE} = 0V, T_A = -40°C to 85°C

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
V_{OH}	Output High Voltage; NOTE 1		V_{CCO} – 1.10		V_{CCO} – 0.75	V
V_{OL}	Output Low Voltage; NOTE 1		V_{CCO} – 2.0		V_{CCO} – 1.60	V
V_{SWING}	Peak-to-Peak Output Voltage Swing		0.6		1.0	V

NOTE 1: Outputs terminated with 50Ω to V_{CCO} – 2V. See Parameter Measurement Information section, *3.3V Output Load Test Circuit.*

Table 4E. LVDS DC Characteristics, V_{CC} = V_{CCO} = V_{CCX} = 3.3V ± 5%, V_{EE} = 0V, T_A = -40°C to 85°C

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
V_{OD}	Differential Output Voltage		247		454	mV
ΔV_{OD}	V_{OD} Magnitude Change				60	mV
V_{OS}	Offset Voltage		1.125		1.375	V
ΔV_{OS}	V_{OS} Magnitude Change				50	mV

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AC Electrical Characteristics

Table 5. AC Characteristics, V_{CC} = V_{CCO} = V_{CCX} = 3.3V ± 5%, V_{EE} = 0V, T_A = 0°C to 70°C

Symbol	Parameter		Test Conditions	Minimum	Typical	Maximum	Units
f_{IN}	Input Frequency		25MHz crystal Frequency	0.008		155.52	MHz
f_{OUT}	Output Frequency			25		312.5	MHz
*t*jit(Ø)	RMS Phase Jitter, (Random); NOTE 1		f_{OUT} = 125MHz, 156.25MHz, 312.5MHz, 25MHz crystal, Integration Range: 12kHz – 20MHz		0.3	0.7	ps
*t*jit(pk-pk)	Peak-to-Peak Jitter	QA	1e -12BER			60	ps
		QB	1e -12BER			25	ps
*t*sk(o)	Output Skew; NOTE 2, 3					75	ps
t_R / t_F	Output Rise/Fall Time	QA	20% to 80%	150		400	ps
		QB	20% to 80%	150		500	ps
odc	Output Duty Cycle			48		52	%
t_{LOCK}	PLL Lock Time				6		s

NOTE: Electrical parameters are guaranteed over the specified ambient operating temperature range, which is established when the device is mounted in a test socket with maintained transverse airflow greater than 500 lfpm. The device will meet specifications after thermal equilibrium has been reached under these conditions.
NOTE: Characterized with outputs at the same frequency using the loop filter components for the mid loop bandwidth.
Refer to VCXO-PLL Loop Bandwidth Selection Table.
NOTE 1: Refer to the Phase Noise Plot.
NOTE 2: This parameter is defined in accordance with JEDEC Standard 65.
NOTE 3: Defined as skew between outputs at the same supply voltage. Measured at the output differential cross points.

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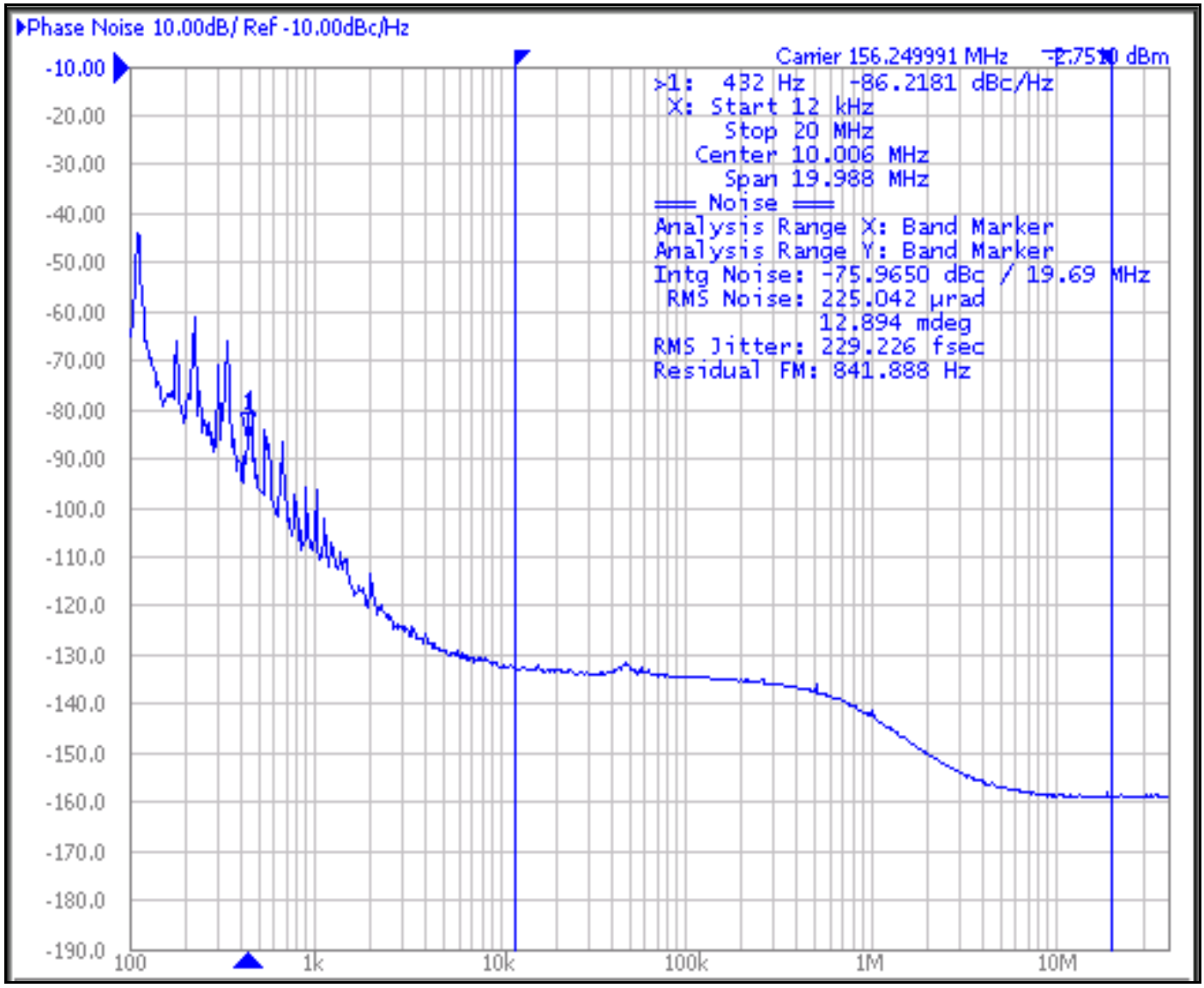
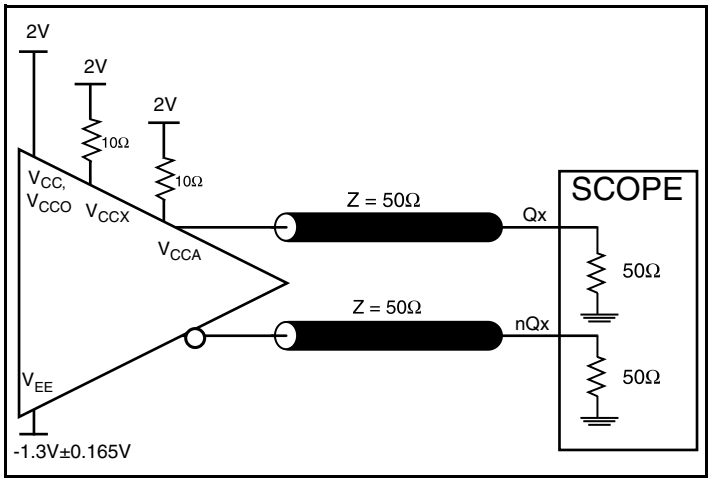
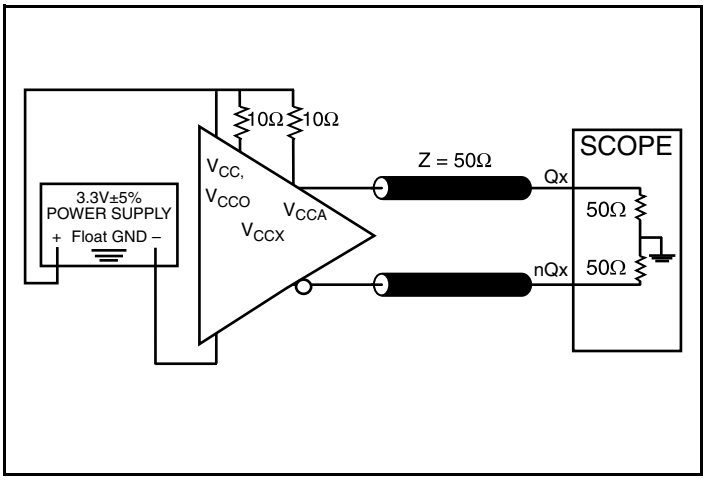
Typical Phase Noise



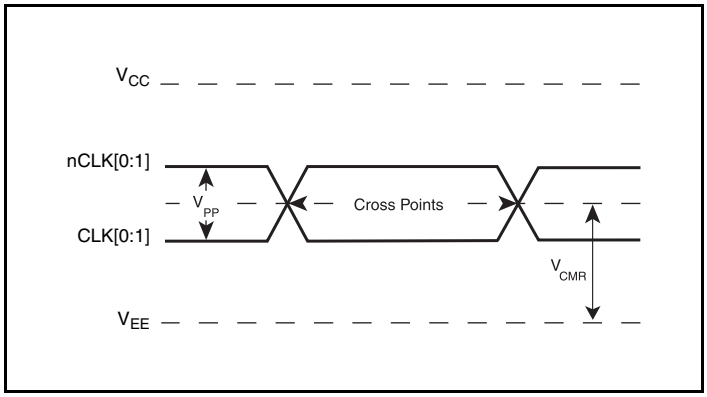
Parameter Measurement Information



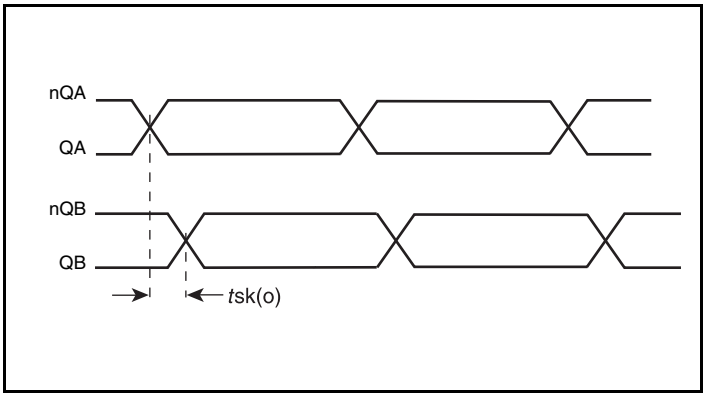
3.3V LVPECL Output Load Test Circuit



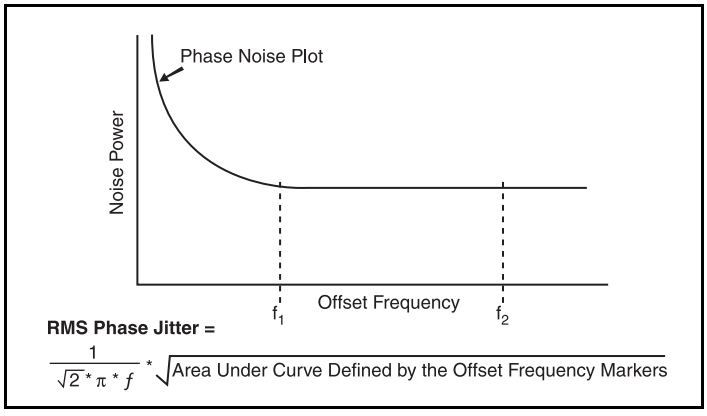
3.3V LVDS Output Load Test Circuit



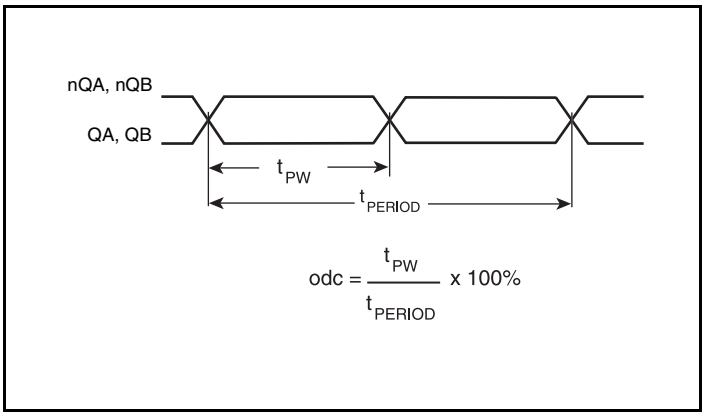
Differential Input Level



Output Skew

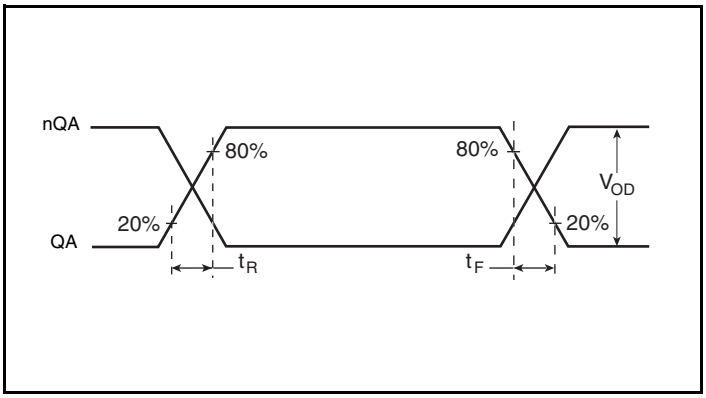


RMS Phase Jitter

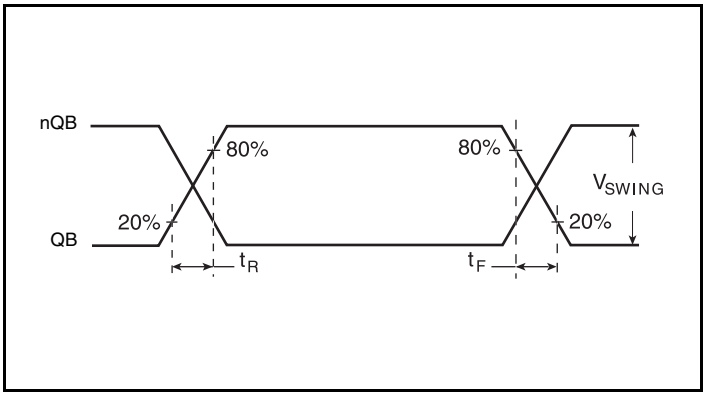


Output Duty Cycle/Pulse Width/Period

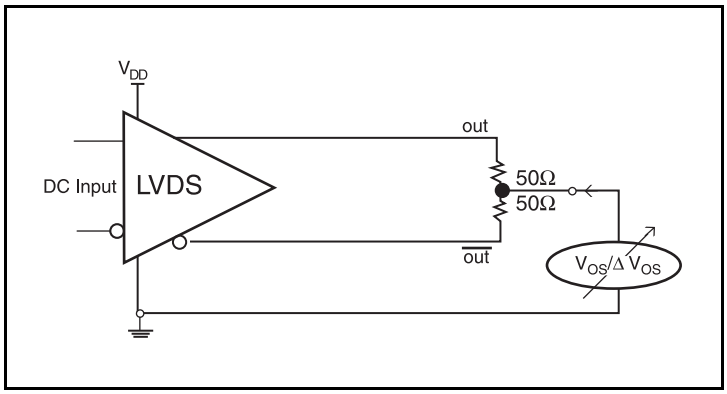
Parameter Measurement Information, continued



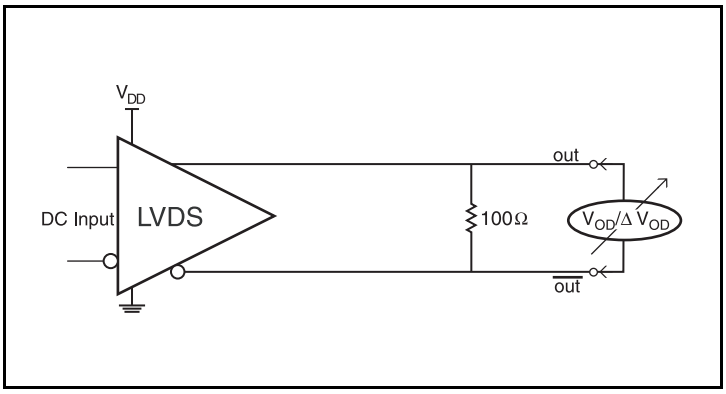
LVDS Output Rise/Fall Time



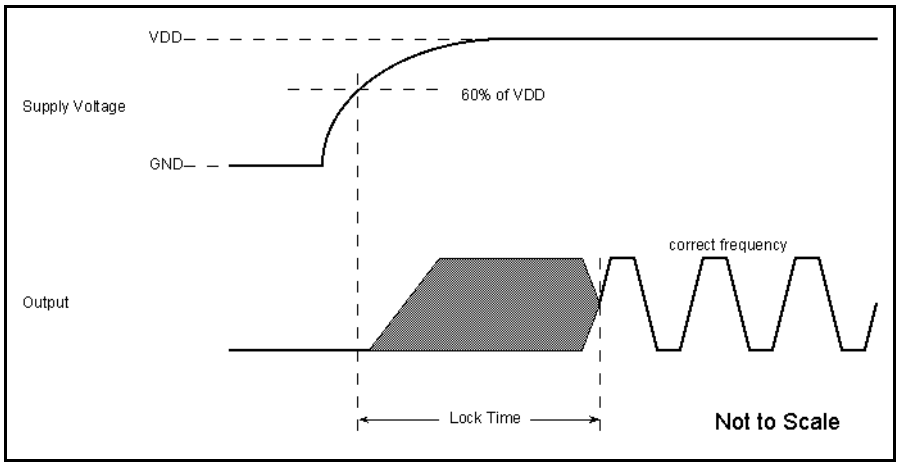
LVPECL Output Rise/Fall Time



Offset Voltage Setup



Differential Output Voltage Setup



VCXO & FemtoClock PLL Lock Time

Applications Information

Power Supply Filtering Technique

As in any high speed analog circuitry, the power supply pins are vulnerable to random noise. To achieve optimum jitter performance, power supply isolation is required. The 813N252I-04 provides separate power supplies to isolate any high switching noise from the outputs to the internal PLL. V_{CC}, V_{CCA}, V_{CCO} and V_{CCX} should be individually connected to the power supply plane through vias, and 0.01µF bypass capacitors should be used for each pin. *Figure 1* illustrates this for a generic V_{CC} pin and also shows that V_{CCA} requires that an additional 10Ω resistor along with a 10µF bypass capacitor be connected to the V_{CCA} pin.

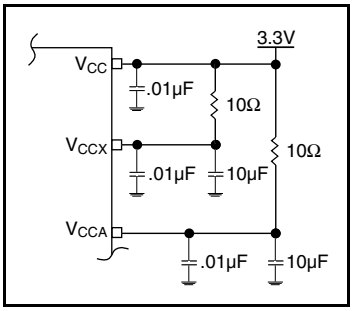


Figure 1. Power Supply Filtering

Wiring the Differential Input to Accept Single-Ended Levels

Figure 2 shows how a differential input can be wired to accept single ended levels. The reference voltage $V_1 = V_{CC}/2$ is generated by the bias resistors R1 and R2. The bypass capacitor (C1) is used to help filter noise on the DC bias. This bias circuit should be located as close to the input pin as possible. The ratio of R1 and R2 might need to be adjusted to position the V_1 in the center of the input voltage swing. For example, if the input clock swing is 2.5V and V_{CC} = 3.3V, R1 and R2 value should be adjusted to set V_1 at 1.25V. Similarly, if the input clock swing is 1.8V and V_{CC} = 3.3V, R1 and R2 value should be adjusted to set V_1 at 0.9V. It is recommended to always use R1 and R2 to provide a known V_1 voltage. The values below are for when both the single ended swing and V_{CC} are at the same voltage. This configuration requires that the sum of the output impedance of the driver (Ro) and the series resistance (Rs) equals the transmission line impedance. In addition, matched termination at the input will attenuate the signal in half. This can be done in one of two ways.

First, R3 and R4 in parallel should equal the transmission line impedance. For most 50Ω applications, R3 and R4 can be 100Ω. The values of the resistors can be increased to reduce the loading for slower and weaker LVCMOS driver. When using single-ended signaling, the noise rejection benefits of differential signaling are reduced. Even though the differential input can handle full rail LVCMOS signaling, it is recommended that the amplitude be reduced. The datasheet specifies a lower differential amplitude, however this only applies to differential signals. For single-ended applications, the swing can be larger, however V_{IL} cannot be less than -0.3V and V_{IH} cannot be more than V_{CC} + 0.3V. Though some of the recommended components might not be used, the pads should be placed in the layout. They can be utilized for debugging purposes. The datasheet specifications are characterized and guaranteed by using a differential signal.

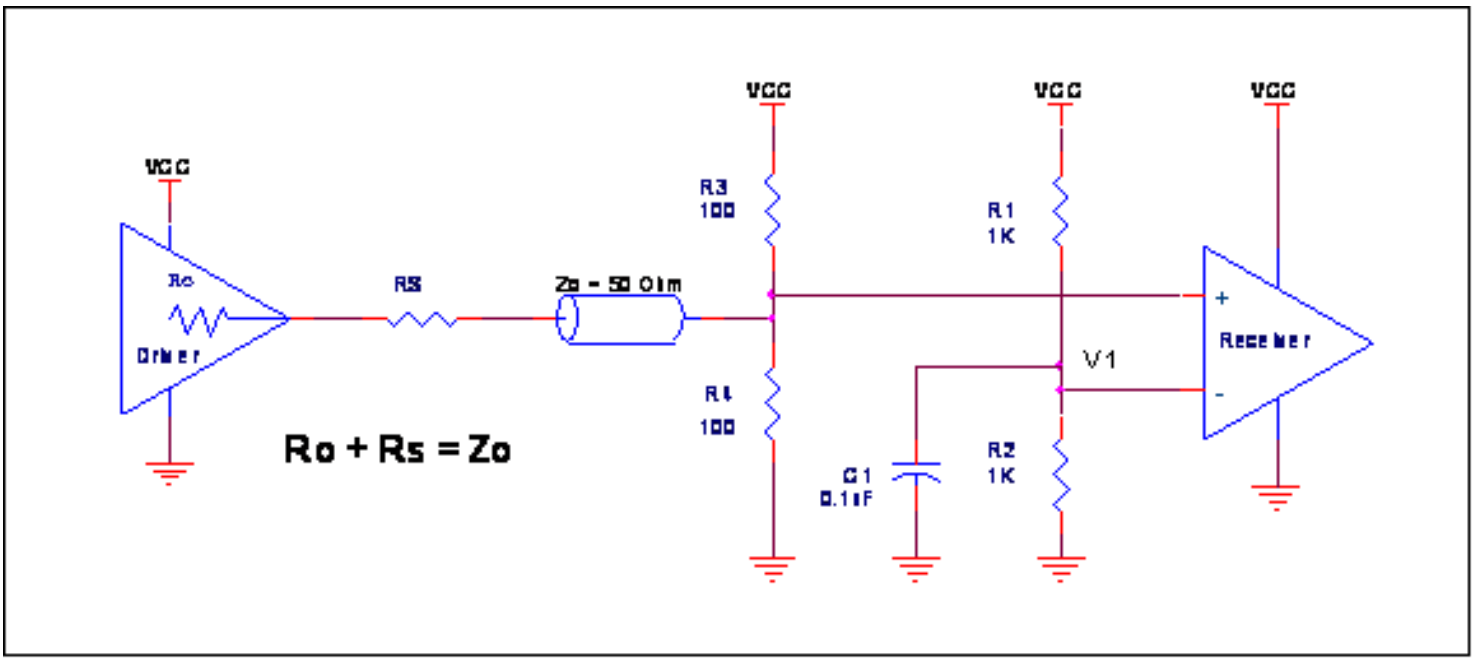


Figure 2. Recommended Schematic for Wiring a Differential Input to Accept Single-ended Levels

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Differential Clock Input Interface

The CLK /nCLK accepts LVDS, LVPECL, LVHSTL, SSTL, HCSL and other differential signals. Both V_{SWING} and V_{OH} must meet the V_{PP} and V_{CMR} input requirements. *Figures 3A to 3F* show interface examples for the CLK/nCLK input driven by the most common driver types. The input interfaces suggested here are examples only.

Please consult with the vendor of the driver component to confirm the driver termination requirements. For example, in Figure 3A, the input termination applies for IDT open emitter LVHSTL drivers. If you are using an LVHSTL driver from another vendor, use their termination recommendation.

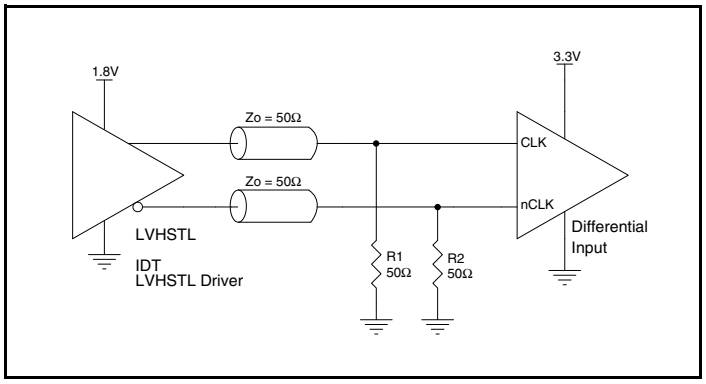


Figure 3A. CLK/nCLK Input Driven by an IDT Open Emitter LVHSTL Driver

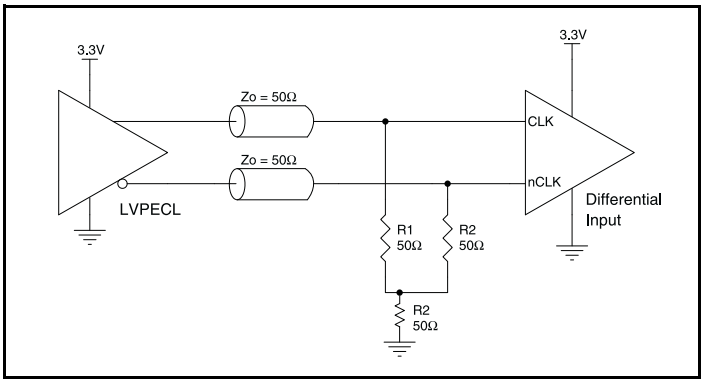


Figure 3B. CLK/nCLK Input Driven by a 3.3V LVPECL Driver

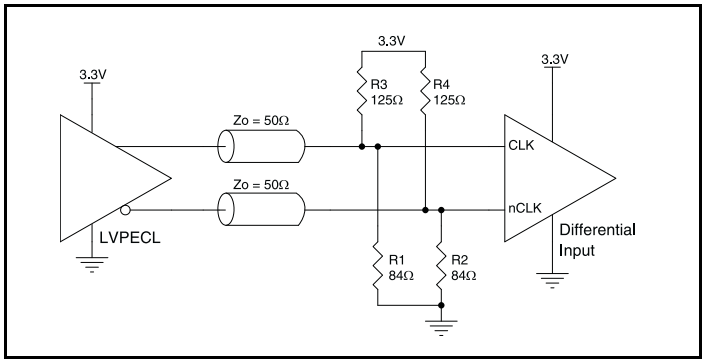


Figure 3C. CLK/nCLK Input Driven by a 3.3V LVPECL Driver

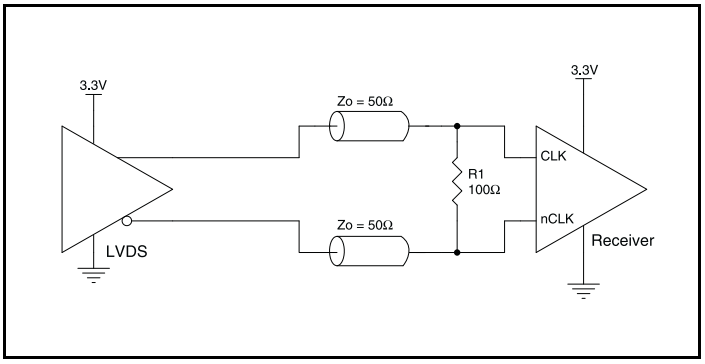


Figure 3D. CLK/nCLK Input Driven by a 3.3V LVDS Driver

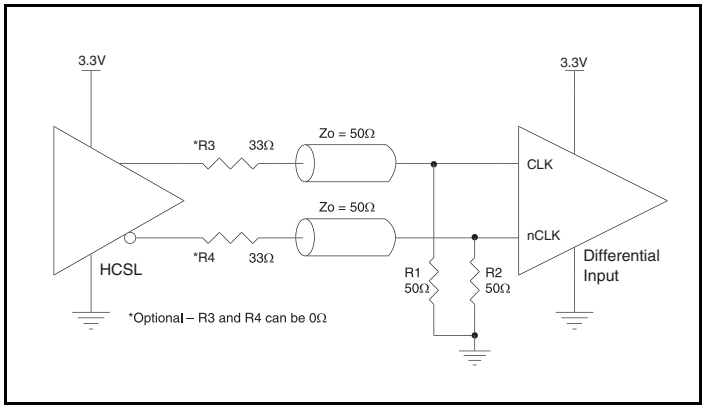


Figure 3E. CLK/nCLK Input Driven by a 3.3V HCSL Driver

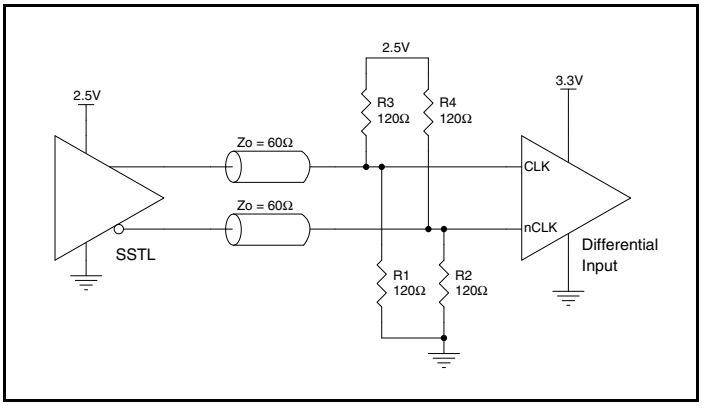


Figure 3F. CLK/nCLK Input Driven by a 2.5V SSTL Driver

Recommendations for Unused Input and Output Pins

Inputs:

CLK/nCLK Inputs

For applications not requiring the use of the differential input, both CLK and nCLK can be left floating. Though not required, but for additional protection, a 1kΩ resistor can be tied from CLK to ground.

LVCMOS Control Pins

All control pins have internal pullups or pulldowns; additional resistance is not required but can be added for additional protection. A 1kΩ resistor can be used.

Outputs:

LVPECL Outputs

All unused LVPECL output pairs can be left floating. We recommend that there is no trace attached. Both sides of the differential output pair should either be left floating or terminated.

LVDS Outputs

All unused LVDS output pairs can be either left floating or terminated with 100Ω across. If they are left floating, there should be no trace attached.

Termination for 3.3V LVPECL Outputs

The clock layout topology shown below is a typical termination for LVPECL outputs. The two different layouts mentioned are recommended only as guidelines.

The differential outputs are low impedance follower outputs that generate ECL/LVPECL compatible outputs. Therefore, terminating resistors (DC current path to ground) or current sources must be used for functionality. These outputs are designed to drive 50Ω transmission lines. Matched impedance techniques should be used to maximize operating frequency and minimize signal distortion. *Figures 4A and 4B* show two different layouts which are recommended only as guidelines. Other suitable clock layouts may exist and it would be recommended that the board designers simulate to guarantee compatibility across all printed circuit and clock component process variations.

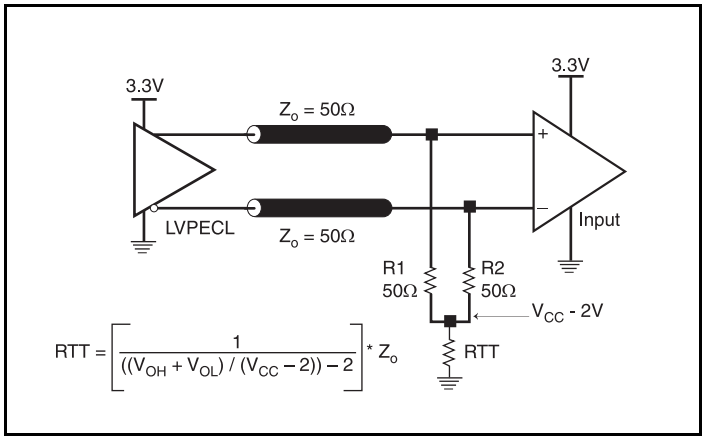


Figure 4A. 3.3V LVPECL Output Termination

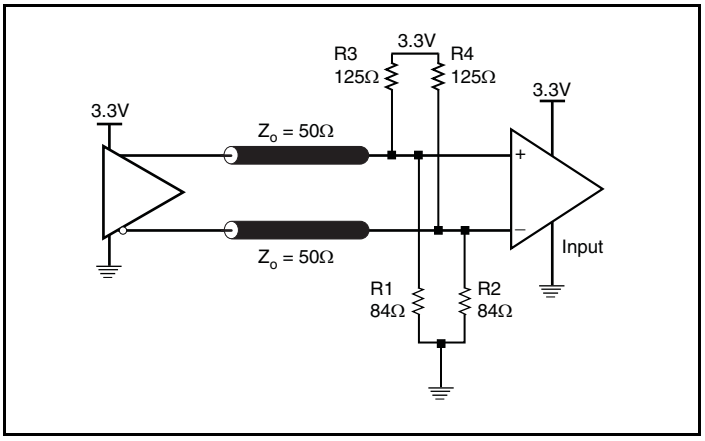


Figure 4B. 3.3V LVPECL Output Termination

LVDS Driver Termination

For a general LVDS interface, the recommended value for the termination impedance (Z_T) is between 90Ω and 132Ω. The actual value should be selected to match the differential impedance (Z_0) of your transmission line. A typical point-to-point LVDS design uses a 100Ω parallel resistor at the receiver and a 100Ω differential transmission-line environment. In order to avoid any transmission-line reflection issues, the components should be surface mounted and must be placed as close to the receiver as possible. IDT offers a full line of LVDS compliant devices with two types of output structures: current source and voltage source. The standard termination schematic as shown in *Figure 5A* can be used with either type of output structure. *Figure 5B*, which can also be used with both output types, is an optional termination with center tap capacitance to help filter common mode noise. The capacitor value should be approximately 50pF. If using a non-standard termination, it is recommended to contact IDT and confirm if the output structure is current source or voltage source type. In addition, since these outputs are LVDS compatible, the input receiver's amplitude and common-mode input range should be verified for compatibility with the output.

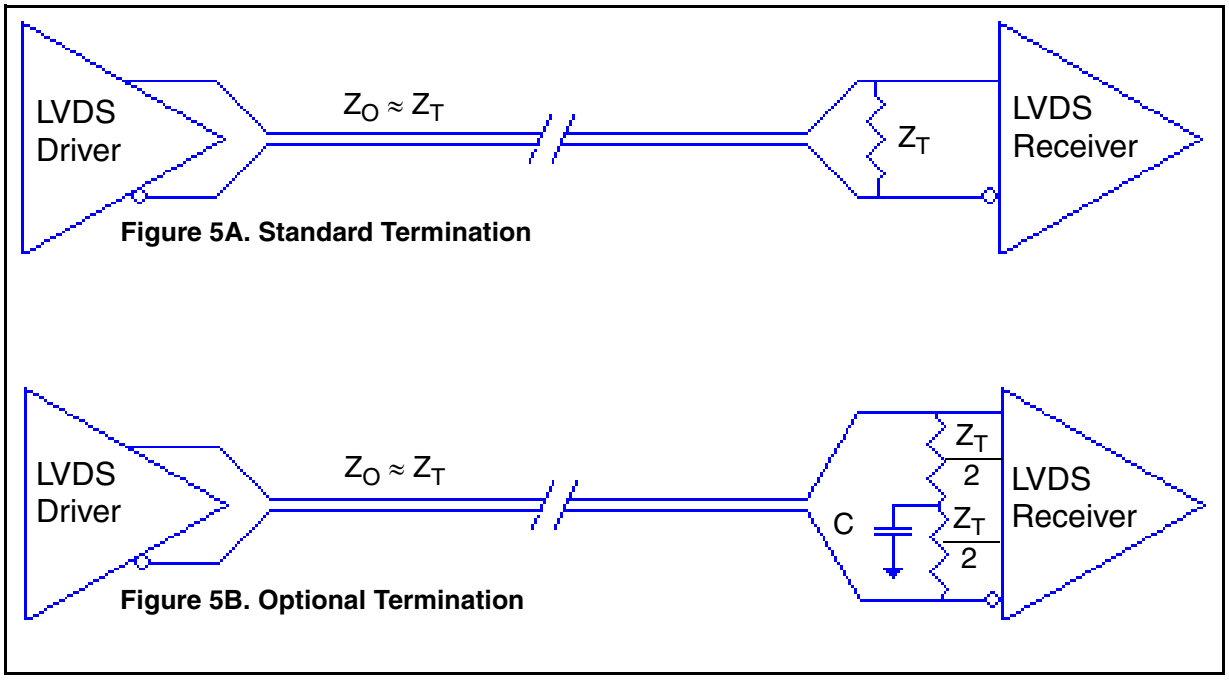


Figure 5A. Standard Termination

Figure 5B. Optional Termination

LVDS Termination

VFQFN EPAD Thermal Release Path

In order to maximize both the removal of heat from the package and the electrical performance, a land pattern must be incorporated on the Printed Circuit Board (PCB) within the footprint of the package corresponding to the exposed metal pad or exposed heat slug on the package, as shown in *Figure 6*. The solderable area on the PCB, as defined by the solder mask, should be at least the same size/shape as the exposed pad/slug area on the package to maximize the thermal/electrical performance. Sufficient clearance should be designed on the PCB between the outer edges of the land pattern and the inner edges of pad pattern for the leads to avoid any shorts.

While the land pattern on the PCB provides a means of heat transfer and electrical grounding from the package to the board through a solder joint, thermal vias are necessary to effectively conduct from the surface of the PCB to the ground plane(s). The land pattern must be connected to ground through these vias. The vias act as “heat pipes”. The number of vias (i.e. “heat pipes”) are application specific and dependent upon the package power dissipation as well as electrical conductivity requirements. Thus, thermal and electrical analysis and/or testing are recommended to determine the minimum number needed. Maximum thermal and electrical performance is achieved when an array of vias is incorporated in the land pattern. It is recommended to use as many vias connected to ground as possible. It is also recommended that the via diameter should be 12 to 13mils (0.30 to 0.33mm) with 1oz copper via barrel plating. This is desirable to avoid any solder wicking inside the via during the soldering process which may result in voids in solder between the exposed pad/slug and the thermal land. Precautions should be taken to eliminate any solder voids between the exposed heat slug and the land pattern. Note: These recommendations are to be used as a guideline only. For further information, please refer to the Application Note on the Surface Mount Assembly of Amkor’s Thermally/ Electrically Enhance Leadframe Base Package, Amkor Technology.

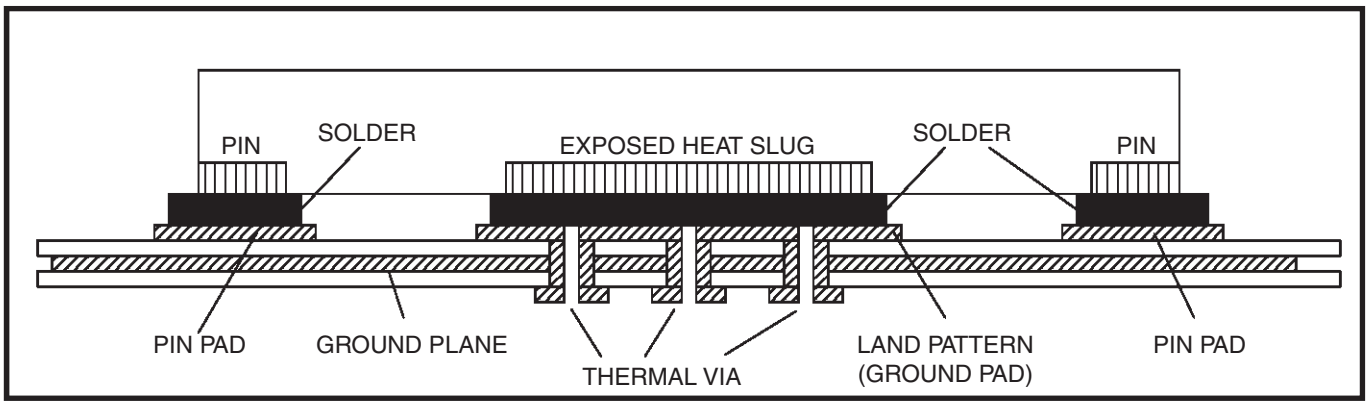


Figure 6. P.C. Assembly for Exposed Pad Thermal Release Path – Side View (drawing not to scale)

Schematic Example

Figure 7 shows an example of 813N252I-04 application schematic. In this example, the device is operated at V_{CC} = V_{CCX} = V_{CCO} = 3.3V. The decoupling capacitors should be located as close as possible to the power pin. The input is driven by a 3.3V LVPECL driver. Two examples of LVPECL and one example of LVDS terminations are shown in this schematic. An optional 3-pole filter can also be used for additional spur reduction. It is recommended that the loop filter components be laid out for the 3-pole option. This will also allow the 2-pole filter to be used.

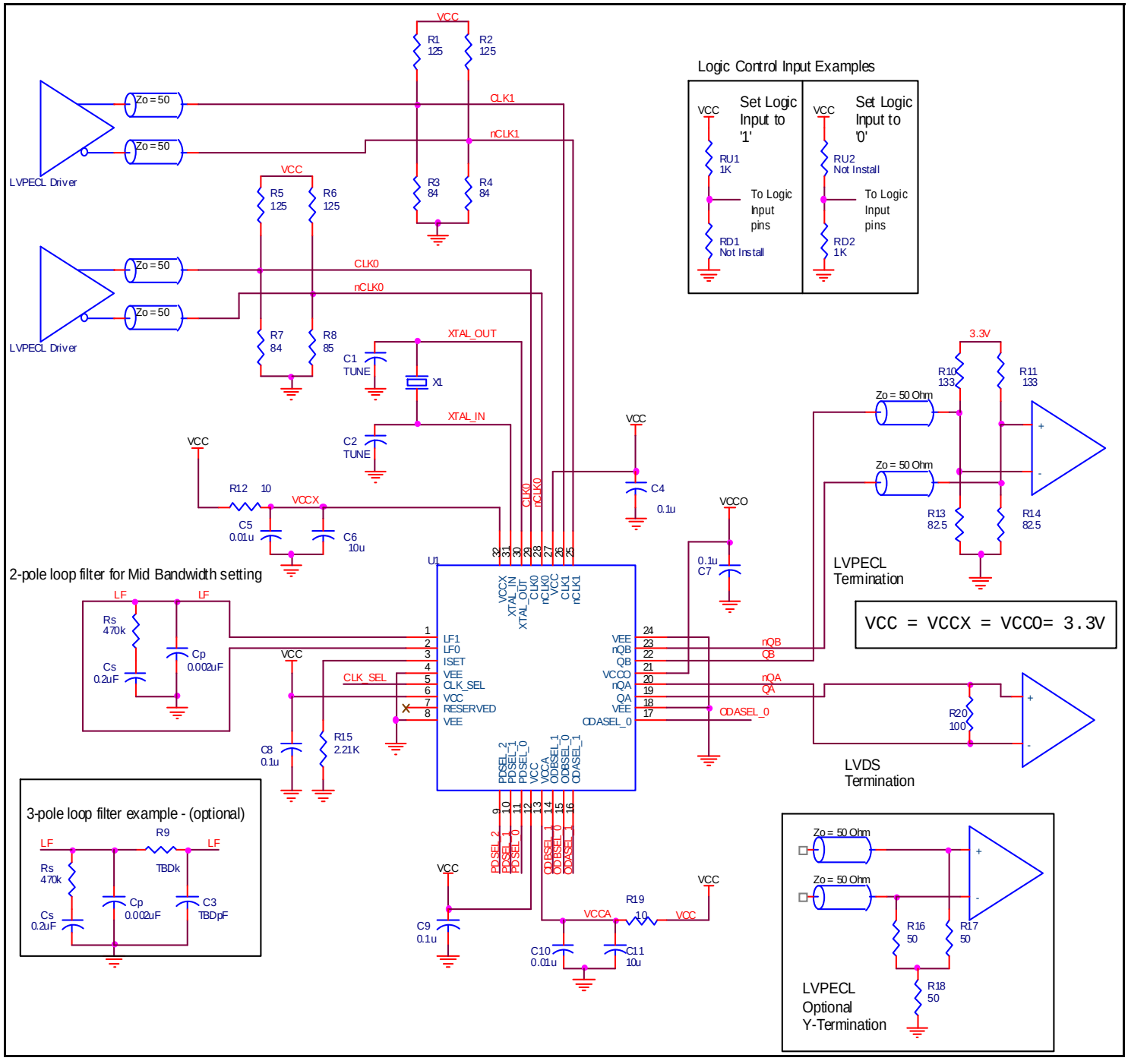


Figure 7. 813N252I-04 Schematic Example

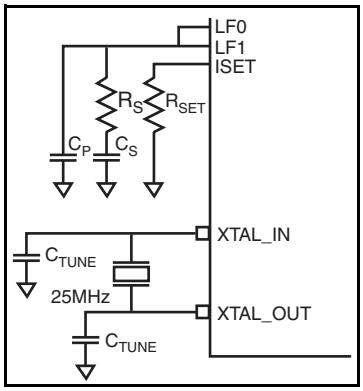
VCXO-PLL External Components

Choosing the correct external components and having a proper printed circuit board (PCB) layout is a key task for quality operation of the VCXO-PLL. In choosing a crystal, special precaution must be taken with the package and load capacitance (C_L). In addition, frequency, accuracy and temperature range must also be considered. Since the pulling range of a crystal also varies with the package, it is recommended that a metal-canned package like HC49 be used. Generally, a metal-canned package has a larger pulling range than a surface mounted device (SMD). For crystal selection information, refer to the *VCXO Crystal Selection Application Note.*

The crystal's load capacitance (C_L) characteristic determines its resonating frequency and is closely related to the VCXO tuning range. The total external capacitance seen by the crystal when installed on a board is the sum of the stray board capacitance, IC package lead capacitance, internal varactor capacitance and any installed tuning capacitors (C_{TUNE}).

If the crystal C_L is greater than the total external capacitance, the VCXO will oscillate at a higher frequency than the crystal specification. If the crystal (C_L) is lower than the total external capacitance, the VCXO will oscillate at a lower frequency than the crystal specification. In either case, the absolute tuning range is reduced. The correct value of (C_L) is dependant on the characteristics of the VCXO. The recommended (C_L) in the Crystal Parameter Table balances the tuning range by centering the tuning curve.

The frequency of oscillation in the third overtone mode is not necessarily at exactly three times the fundamental frequency. The mechanical properties of the quartz element dictate the position of the overtones relative to the fundamental. The oscillator circuit may excite both the fundamental and overtone modes simultaneously. This will cause a nonlinearity in the tuning curve. This potential problem is why VCXO crystals are required to be tested for absence of any activity inside a ±200 ppm window at three times the fundamental frequency. Refer to F_{L_3OVT} and $F_{L_3OVT_spurs}$ in the crystal Characteristics table.



The crystal and external loop filter components should be kept as close as possible to the device. Loop filter and crystal traces should be kept short and separated from each other. Other signal traces should be kept separate and not run underneath the device, loop filter or crystal components.

VCXO Characteristics Table

Symbol	Parameter	Typical	Units
k_{VCXO}	VCXO Gain	4.4	kHz/V
C_{V_LOW}	Low Varactor Capacitance	8	pF
C_{V_HIGH}	High Varactor Capacitance	16	pF

VCXO-PLL Loop Bandwidth Selection Table

Bandwidth	Crystal Frequency (MHz)	M	R_S (kΩ)	C_S (µF)	C_P (µF)	R_{SET} (kΩ)
8Hz (Low)	25	3125	680	0.20	0.002	22
20Hz (Mid)	25	3125	470	0.20	0.002	5
75Hz (High)	25	3125	680	0.02	0.0003	2.2

NOTE: When configuring the 813N252I-04 with PLL loop bandwidth less than 75Hz, it is recommended that CLK1, nCLK1 input be used as the only reference clock. In systems where both reference clocks are used, it is recommended to have PLL loop bandwidths of 75Hz or greater.

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Crystal Characteristics

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
	Mode of Oscillation			Fundamental		
f_N	Frequency			25		MHz
f_T	Frequency Tolerance				±20	ppm
f_S	Frequency Stability				±20	ppm
	Operating Temperature Range		-40		85	^{0}C
C_L	Load Capacitance			10		pF
C_O	Shunt Capacitance			4		pF
C_O / C_1	Pullability Ratio			220	240	
F_{L_3OVT}	3rd Overtone F_L		200			ppm
$F_{L_3OVT_spurs}$	3rd Overtone F_L Spurs		200			ppm
ESR	Equivalent Series Resistance				20	Ω
	Drive Level				1	mW
	Aging @ 25 ^{0}C	First Year			±3	ppm
		Ten Year			±10	ppm

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Power Considerations

This section provides information on power dissipation and junction temperature for the 813N252I-04.
Equations and example calculations are also provided.

1. Power Dissipation.

The total power dissipation for the 813N252I-04 is the sum of the core power plus the power dissipated in the load(s).
The following is the power dissipation for V_{CC} = 3.3V + 5% = 3.465V, which gives worst case results.

NOTE: Please refer to Section 3 for details on calculating power dissipated in the load.

- Power (core_LVDS)$_{MAX}$ = V_{CC_MAX} * I_{EE_MAX} = 3.465V * 225mA = **779.625mW**
- Power (outputs)$_{MAX}$ = **31.55mW/Loaded Output pair**

Total Power$_{_MAX}$ (3.465V, with all outputs switching) = 779.625mW + 31.55mW = **811.175mW**

2. Junction Temperature.

Junction temperature, Tj, is the temperature at the junction of the bond wire and bond pad directly affects the reliability of the device. The maximum recommended junction temperature is 125°C. Limiting the internal transistor junction temperature, Tj, to 125°C ensures that the bond wire and bond pad temperature remains below 125°C.

The equation for Tj is as follows: Tj = θ_{JA} * Pd_total + T_A

Tj = Junction Temperature

θ_{JA} = Junction-to-Ambient Thermal Resistance

Pd_total = Total Device Power Dissipation (example calculation is in section 1 above)

T_A = Ambient Temperature

In order to calculate junction temperature, the appropriate junction-to-ambient thermal resistance θ_{JA} must be used. Assuming no air flow and a multi-layer board, the appropriate value is 37°C/W per Table 6 below.

Therefore, Tj for an ambient temperature of 85°C with all outputs switching is:

85°C + 0.811W * 37°C/W = 115°C. This is below the limit of 125°C.

This calculation is only an example. Tj will obviously vary depending on the number of loaded outputs, supply voltage, air flow and the type of board (multi-layer).

Table 6. Thermal Resistance θ_{JA} for 32 Lead VFQFN, Forced Convection

θ_{JA} by Velocity			
Meters per Second	**0**	**1**	**2.5**
Multi-Layer PCB, JEDEC Standard Test Boards	37.0°C/W	32.4°C/W	29°C/W

3. Calculations and Equations.

The purpose of this section is to calculate the power dissipation for the LVPECL output pair.

LVPECL output driver circuit and termination are shown in *Figure 8.*

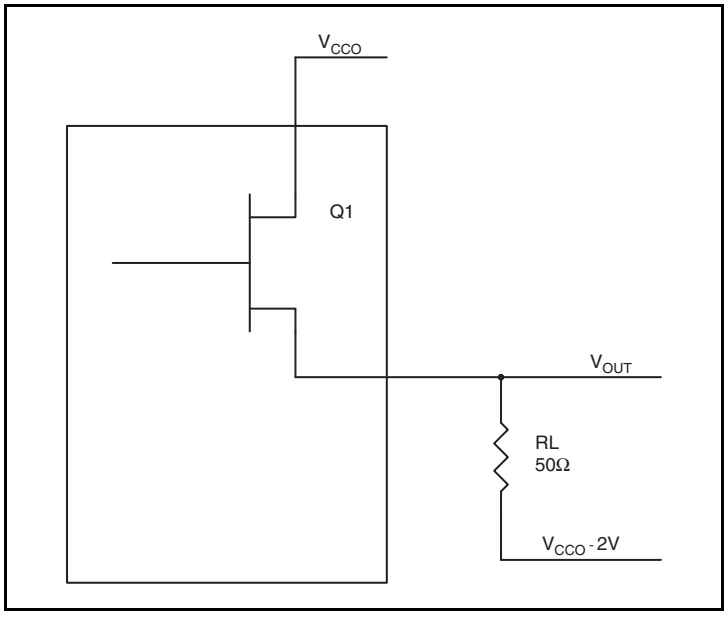

Figure 8. LVPECL Driver Circuit and Termination

To calculate power dissipation per output pair due to loading, use the following equations which assume a 50Ω load, and a termination voltage of V_{CCO} – 2V.

- For logic high, $V_{OUT} = V_{OH_MAX} = \mathbf{V_{CCO_MAX} - 0.75V}$
  $(V_{CCO_MAX} - V_{OH_MAX}) = \mathbf{0.75V}$
- For logic low, $V_{OUT} = V_{OL_MAX} = \mathbf{V_{CCO_MAX} - 1.6V}$
  $(V_{CCO_MAX} - V_{OL_MAX}) = \mathbf{1.6V}$

Pd_H is power dissipation when the output drives high.

Pd_L is the power dissipation when the output drives low.

$Pd_H = [(V_{OH_MAX} – (V_{CCO_MAX} – 2V))/R_L] * (V_{CCO_MAX} – V_{OH_MAX}) = [(2V – (V_{CCO_MAX} – V_{OH_MAX}))/R_L] * (V_{CCO_MAX} – V_{OH_MAX}) = [(2V – 0.75V)/50Ω] * 0.75V =$ **18.75mW**

$Pd_L = [(V_{OL_MAX} – (V_{CCO_MAX} – 2V))/R_L] * (V_{CCO_MAX} – V_{OL_MAX}) = [(2V – (V_{CCO_MAX} – V_{OL_MAX}))/R_L] * (V_{CCO_MAX} – V_{OL_MAX}) = [(2V – 1.6V)/50Ω] * 1.6V =$ **12.80mW**

Total Power Dissipation per output pair = Pd_H + Pd_L = **31.55mW**

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Reliability Information

Table 7. θ_{JA} vs. Air Flow Table for a 32 Lead VFQFN

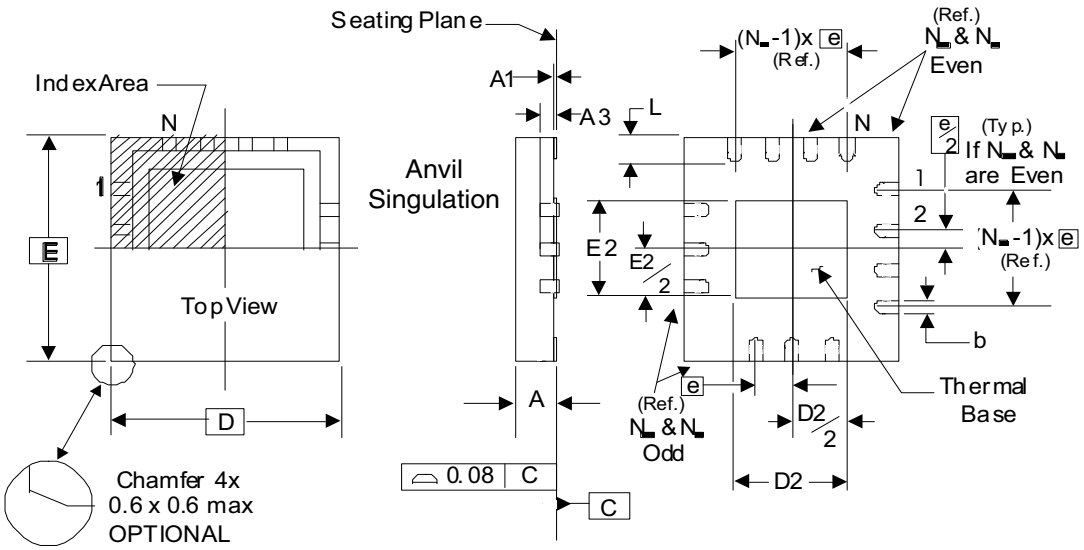
θ_{JA} vs. Air Flow			
Meters per Second	**0**	**1**	**2.5**
Multi-Layer PCB, JEDEC Standard Test Boards	37.0°C/W	32.4°C/W	29°C/W

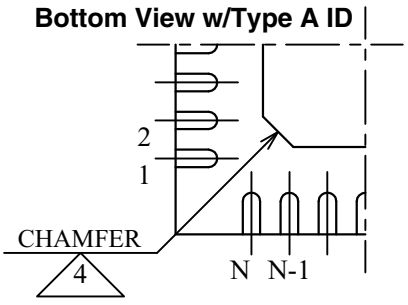
Transistor Count

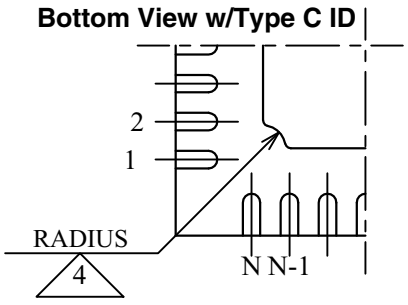
The transistor count for 813N252I-04 is: 22,280

Package Outline and Package Dimensions

Package Outline - K Suffix for 32 Lead VFQFN







There are 2 methods of indicating pin 1 corner at the back of the VFQFN package:

1. Type A: Chamfer on the paddle (near pin 1)
2. Type C: Mouse bite on the paddle (near pin 1)

Table 8. Package Dimensions

JEDEC Variation: VHHD-2/-4 All Dimensions in Millimeters			
Symbol	**Minimum**	**Nominal**	**Maximum**
N		32	
A	0.80		1.00
A1	0		0.05
A3		0.25 Ref.	
b	0.18	0.25	0.30
N_D & N_E			8
D & E		5.00 Basic	
D2 & E2	3.0		3.3
e		0.50 Basic	
L	0.30	0.40	0.50

Reference Document: JEDEC Publication 95, MO-220

NOTE: The following package mechanical drawing is a generic drawing that applies to any pin count VFQFN package. This drawing is not intended to convey the actual pin count or pin layout of this device. The pin count and pin out are shown on the front page. The package dimensions are in Table 8.

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Ordering Information

Table 9. Ordering Information

Part/Order Number	Marking	Package	Shipping Packaging	Temperature
813N252BKI-04LF	ICS252BI04L	“Lead-Free” 32 Lead VFQFN	Tray	-40°C to 85°C
813N252BKI-04LFT	ICS252BI04L	“Lead-Free” 32 Lead VFQFN	Tape & Reel	-40°C to 85°C

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Revision History Sheet

Rev	Table	Page	Description of Change	Date
A	4C 4D	7 7 12	Differential DC Characteristics Table - redefined VCMR min. to standard levels as the crosspoint. Changed from 0.5V min. to V_{EE}. Updated Notes. LVPECL DC Characteristics Table - corrected V_{OH}/V_{OL} Parameter verbiage from Current to Voltage and corrected units to “V”. Updated “Wiring the Differential Input to Accept Single-ended Levels”.	3/18/10
A		6	Supply Voltage, $V_{CC.}$ Rating changed from 4.5V min. to 3.63V per Errata NEN-11-03.	5/24/11
B		 11 12 15 18 22 T9 23	Per PCN #N1210-01 changed revision marking from “A” to “B” in page footer and ordering information table. Parameter Measurement Information Section - added LockTime diagram. Updated *Wiring the Differential Input to Accept Single-ended Levels* Application Note. Updated *LVDS Driver Termination* Application Note. VCXO-PLL External Components: VCXO-PLL Loop Bandwidth Selection Table - added note. Crystal Characteristics - added “Ten Year” spec to *Aging* row. Updated Package Outline. Ordering Information Table - changed revision marking from “A” to “B”; deleted Tape & Reel Count; deleted note.	1/18/13
C			Updated header/footer. Deleted “ICS” prefix from part number.	12/11/15

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(Rev.1.0 Mar 2020)

Corporate Headquarters

TOYOSU FORESIA, 3-2-24 Toyosu,
Koto-ku, Tokyo 135-0061, Japan
www.renesas.com

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